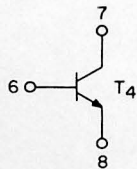
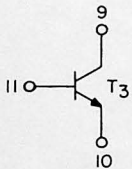
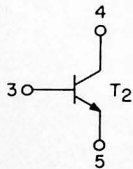
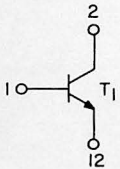


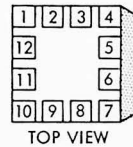
Functional Description

The Four Transistor, FTX-1C, module consists of four single transistors with the individual base, emitter and collector leads terminated at specific pins. The four transistor module offers the circuit designer uniformity of circuit packaging as well as flexibility in application with other SLT modules.

Schematic



Terminal Configuration



Mechanical
Chamfer
Right Side

TOP VIEW

Maximum Ratings

$$I_E = 50 \text{ milliamps}$$

FTX-1C Test Conditions

INDIVIDUAL DEVICE PARAMETER TESTS					
TESTS	TEST CONDITIONS	T ° C	LIMITS		
			MIN	MAX	UNITS
I_{CEX}	$V_{CE} = +13V, V_{BE} = +0.35V$	75		20	μa
I_{BEX}	$V_{CE} = 13V, V_{BE} = -2.5V$	75		10	μa
V_{CEO}	$I_C = 5 \text{ ma}$	25	10		V
V_{EBO}	$I_E = 10 \mu a$	25	2.5		V
V_{CBO}	$I_C = 10 \mu a$	25	15		V
h_{FE1}	$I_E = .1 \text{ ma}, V_{CB} = 0.0V$	25	10		—
h_{FE2}	$I_E = 1 \text{ ma}, V_{CB} = 0.0V$	25	25		—
h_{FE3}	$I_E = 10 \text{ ma}, V_{CB} = 0.0V$	25	30		—
h_{FE4}	$I_E = 50 \text{ ma}, V_{CB} = 0.0V$	25	25		—
$V_{CE1}(\text{sat})$	$I_C = 1 \text{ ma}, I_B = 0.05 \text{ ma}$	25		0.22	V
$V_{CE2}(\text{sat})$	$I_C = 10 \text{ ma}, I_B = 0.50 \text{ ma}$	25		0.24	V
$V_{CE3}(\text{sat})$	$I_C = 22 \text{ ma}, I_B = 1.2 \text{ ma}$	25		0.32	V
$V_{CE4}(\text{sat})$	$I_C = 50 \text{ ma}, I_B = 2.5 \text{ ma}$	25		0.40	V
$V_{BE1}(\text{sat})$	$I_C = 1 \text{ ma}, I_B = 0.05 \text{ ma}$	25	.60	0.75	V
$V_{BE2}(\text{sat})$	$I_C = 10 \text{ ma}, I_B = 0.50 \text{ ma}$	25	.70	0.85	V
$V_{BE3}(\text{sat})$	$I_C = 50 \text{ ma}, I_B = 2.5 \text{ ma}$	25	.85	1.1	V
$V_{BE(ON)}$	$I_C = 1.0 \text{ ma}, V_{CB} = +1.0V$	75	.50		V
C_{ib}	OV BIAS $f = 1 \pm 0.5 \text{ mhz}$	25		6.0	pf
C_{ob}	OV BIAS $f = 1 \pm 0.5 \text{ mhz}$	25		6.0	pf
/GAIN/	$I_E = 10 \text{ ma}, V_{CB} = 3V, f = 100 \text{ mhz}$ $R_L = 50 \Omega$	25	1.5		—
t_{s1}	$I_C = 10 \text{ ma}, I_{B(ON)} = .33 \text{ ma}$ See Fig 1	25		250	ns
h_{ie}	$I_C = 5.0 \text{ ma}, V_{CE} = +5V, f = 1 \text{ khz}$	25	0.10	2.0	K Ω
h_{fe2}	$I_C = 1.0 \text{ ma}, V_{CE} = +5V, f = 1 \text{ khz}$	25	20	180	—
h_{fe3}	$I_C = 5.0 \text{ ma}, V_{CE} = +5V, f = 1 \text{ khz}$	25	30	250	—
h_{fb}	$I_E = 5.0 \text{ ma}, V_{CB} = +5V, f = 1 \text{ khz}$	25	0	1.6	$\times 10^{-3}$
h_{ob}	$I_E = 5.0 \text{ ma}, V_{CB} = +5V, f = 1 \text{ khz}$	25	0	2.5	$\mu \text{ mho}$

T_s Test Circuit

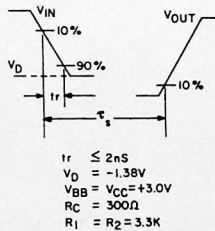
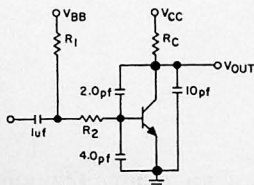


FIGURE 1